

IN THE SPECIFICATION

Please replace the paragraph beginning on page 1, line 24 of the substitute specification with the following:

JP-A -Laid-Open No. 2-224233 discloses a method of processing specimens, comprising: a first step of processing a laminated specimen which includes metals, each having a different ionization tendency, by gas plasma etching using a first gas plasma via a resist mask formed on the lamination in a first processing chamber; a second step of processing the specimen using a second gas plasma, which is formed in a gas atmosphere different from that of the first gas plasma in a second processing chamber, for removing the resist mask and residual corrosive substances formed in the first step and deposited on a surface of side walls of the lamination including different ionization metals; and a third step of rinsing the surface of the specimen which is exposed by the first and the second steps with at least one liquid for removing a remaining part of the residual corrosive substances deposited on the side wall of the lamination which could not have been removed by the second step. According to this method, in the first step, the specimen formed by laminating an Al alloy film and a TiW or TiN film is subjected to etching via a resist mask in a vacuum using a gas plasma which contains chlorine; in the second step, the specimen is subjected to an ashing process using a gas plasma which contains chlorine; and in the third step, the specimen is rinsed in water, and wherein the third step is comprised of either one of the following four steps in order to remove a residual corrosive product remaining after the first step: (a) rinsing in water; (b) rinsing in water after rinsing in alkaline liquid; (c) rinsing in water after rinsing in acid liquid; and (d) rinsing in water after rinsing in fluorine a mixture of hydrofluoric acid

and nitric acid.

Please replace the paragraph beginning on page 8, line 5 of the substitute specification with the following:

The invention, further, provides for the method foregoing of processing the specimen, wherein the second step of liquid rinsing is comprised of one or more of the following steps:

- (A) a pure water rinsing;
- (B) water rinsing after alkaline liquid rinsing (resist developer solution TMAH);
- (C) water rinsing after acid liquid rinsing;
- (D) water rinsing after ~~fluorine-nitric acid~~ rinsing in a mixture of hydrofluoric acid and nitric acid ~~(resist developer solution TMAH)~~; and
- (E) water rinsing after neutral detergent cleaning.